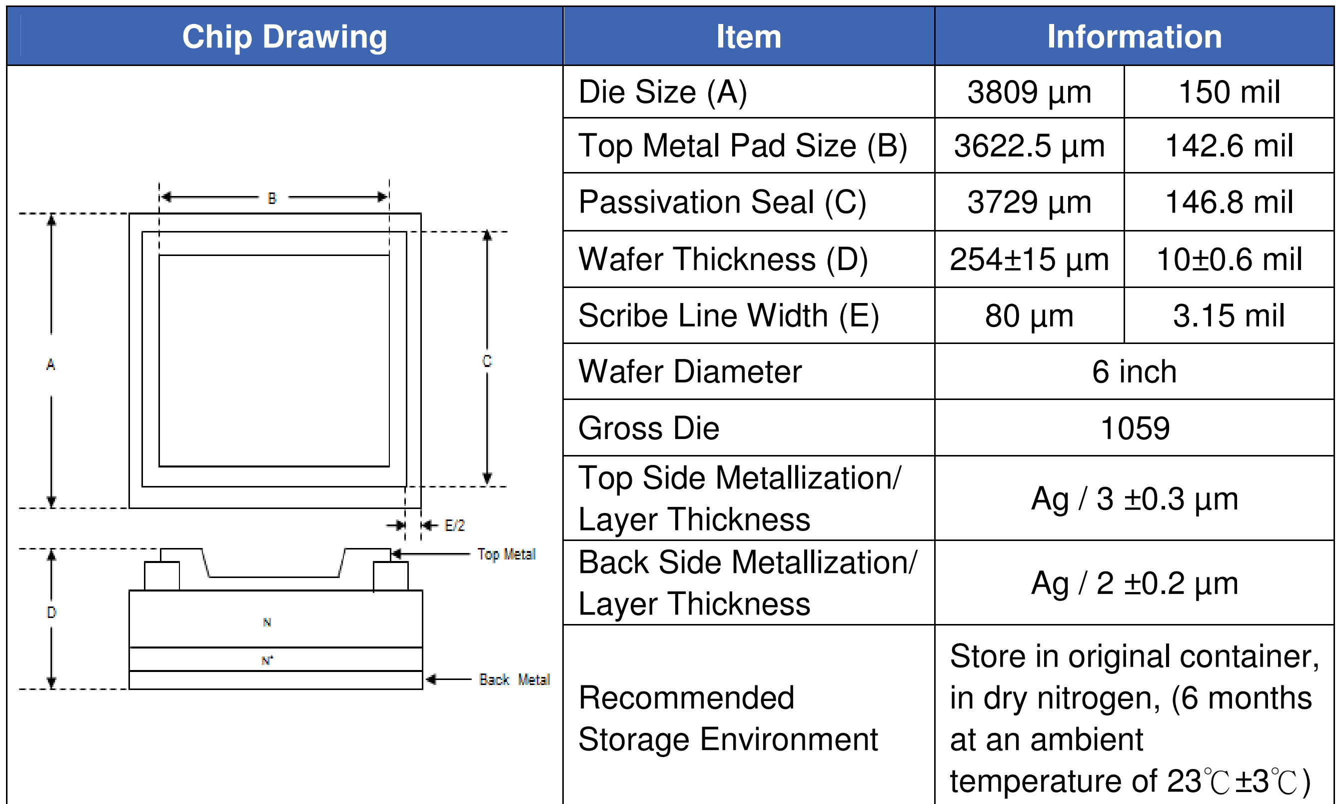
BM0200BG

200V, 30A(1), XTBR series Schottky

Mechanical Data



Chip Drawing	Item	Information	
	Die Size (A)	3809 µm	150 mil
	Top Metal Pad Size (B)	3622.5 µm	142.6 mil
	Passivation Seal (C)	3729 µm	146.8 mil
	Wafer Thickness (D)	254±15 µm	10±0.6 mil
	Scribe Line Width (E)	80 µm	3.15 mil
	Wafer Diameter	6 inch	
	Gross Die	1059	
	Top Side Metallization/ Layer Thickness	Ag / 3 ±0.3 µm	
	Back Side Metallization/ Layer Thickness	Ag / 2 ±0.2 µm	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23℃±3℃)	

Electrical Characteristics in C/P test（T_J =25℃）

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	200	—	—	V	I_R =300µA
V_F	Instantaneous Forward Voltage	—	0.585	0.63	V	I_F =3A(2)
		—	0.745	0.78	V	I_F =10A(2)
I_R	Reverse Leakage Current	—	15.5	25	µA	V_R =200V
T_J, T_{STG}	Operating and Storage Temperature	-40℃ to 150℃ Max				